# DRD1 Workshop Production at MPT workshop



Adam Drozd, Warsaw 09/10/2025

# Outline

```
Micro pattern technologies workshop
        activities
        staffing and infrastructure
Recent large size productions
         HCAL Resistive Micromegas high-rate detector
         HCAL µRwell high-rate detector
         \muRwell for EIC ePIC BOT (barrel outer tracker)
         CLAS 12 µRwell 1 D
Future
        Polyiamide etching machine
```

### MPT activities

Components for the LHC machine

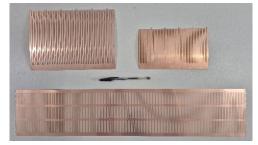
Flexible quench heater (up to 14m long)

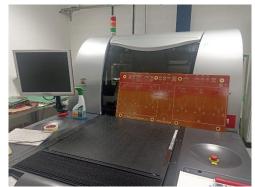
Magnetic sensors for calibration

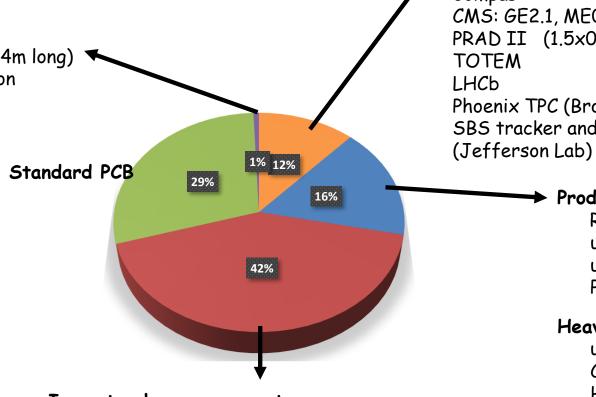
RF fingers

Many chemical milling









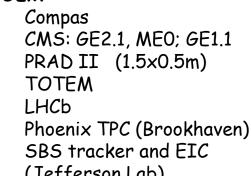
#### Inner trackers components

ATLAS ITK inner tracker long buses  $(1.4 \times 0.15m)$ ~1000 pieces

ATLAS ITK forward power tapes

ATLAS ITK pig tails and PPO flex rigid boards





GEM



#### Production

Resistive BULK Micromegas

uRwell uRgroove Pico Sec



uRwell large size detectors Capacitive sharing detectors High-rate detectors (MM & uRwell) Resistive GEMs Fast timing detectors Low mass uGroove





embedded silicon chips -> 27x10 cm



### MPT staffing and infrastructure

#### MPT Human resources

Rui de Oliveira -> Adam Drozd

- 23 persons:

15 persons from a contracting company

8 CERN staff

#### Wet processing Area

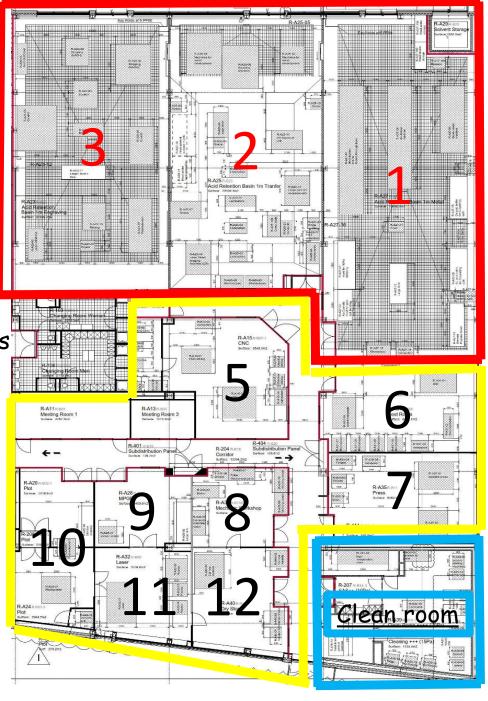
- 1 Plating facility
- 2 Photo processes
- 3 Chemical Etching

#### **Building 107**

- Meyrin site
- 1400 square meters
- moved in 2018

#### Dry processing Area

- 5 Drilling/milling
- 6 Test
- 7 Pressing
- 8 GEMs
- 9 Chemical analysis
- 10 Photo mask lab
- 11 Vacuum deposition
- 12 Dry store



# HCAL - Resistive Micromegas high-rate detector

Double SBU DOT structure

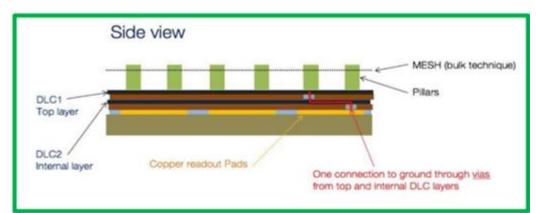
- DLC 20 to 40M

- outer size: 70cm x 54cm

- active area: 50cm x50cm

- pads 11.1mm  $\times$  11.1mm pitch

- 2025 Pads





copper top resistive DLC polyimide bottom

After vacuum gluing







PCB from ELTOS





plating



# HCAL - Resistive Micromegas high-rate detector

Double SBU DOT structure

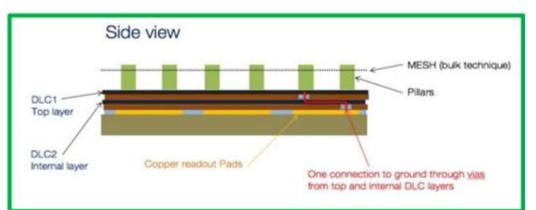
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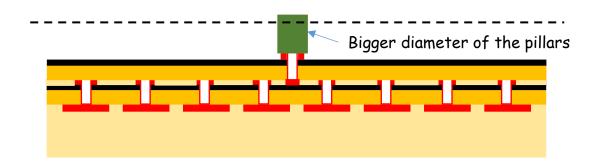








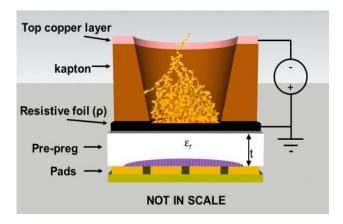
After copper etching, Palting, "bulkage"

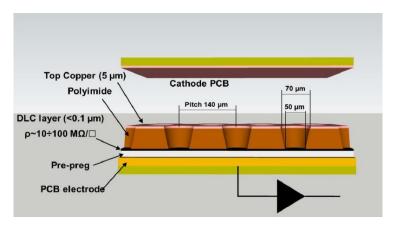




#### Micro Resistive Well

#### **Principles**



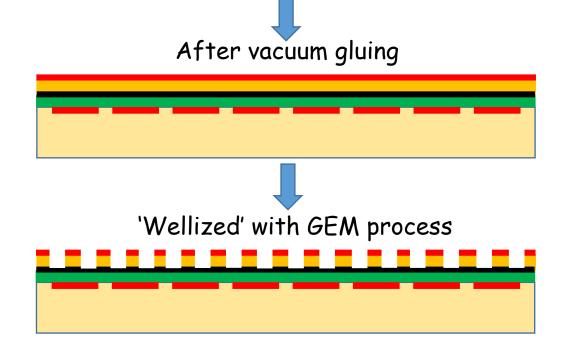


#### **Production steps**

Polyimide coated foil: copper top, resistive DLC layer bottom



Any PCB or flex with any kind of R/O structure X/Y, UVW, Pads, Capacitive sharing etc..



#### **DOT** evacuation structure

-DLC 40 to 80M

-outer size :  $70 \text{cm} \times 54 \text{cm}$ 

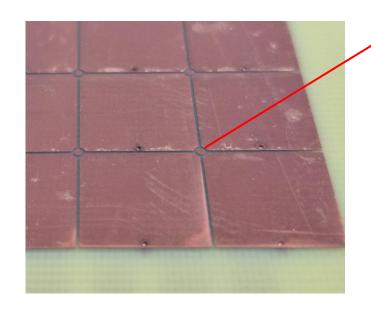
-active area: 50cm x50cm

-pads 11.1mm  $\times$  11.1mm

-2025 Pads







# DOT evacuation structure, connected to back shielding

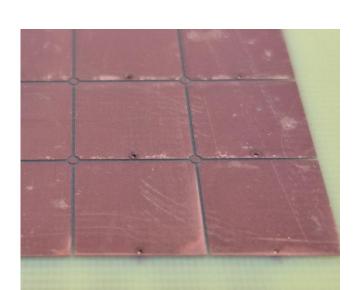
-DLC 40 to 80M

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-2025 Pads







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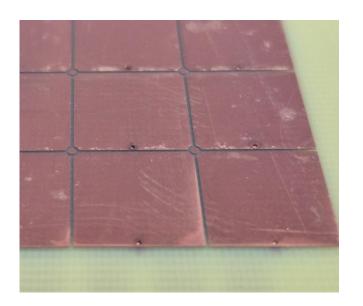
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After vacuum gluing





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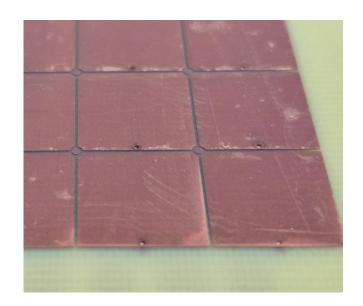
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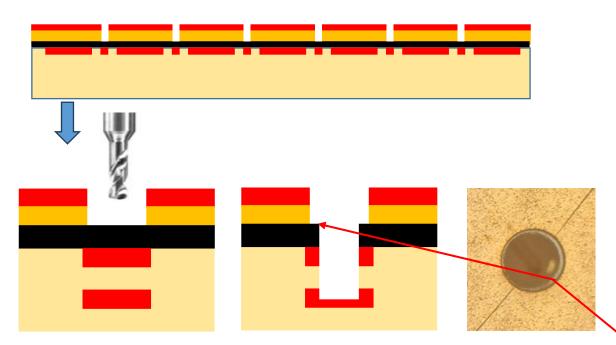
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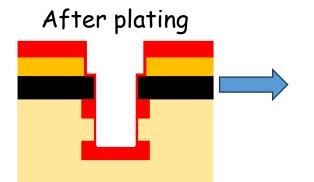
-2025 Pads

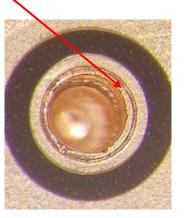












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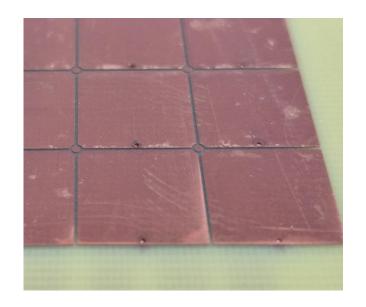
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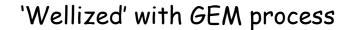
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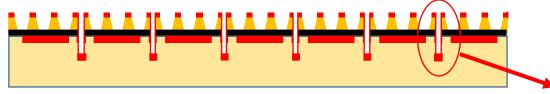
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-2025 Pads



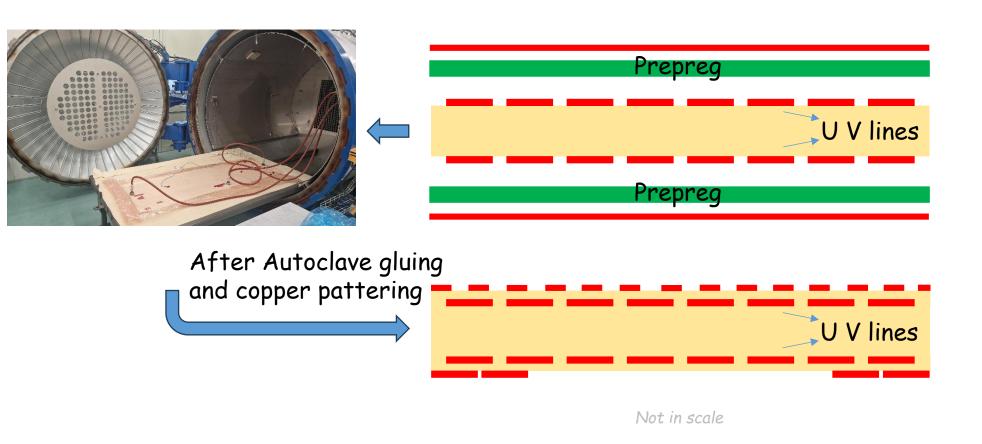






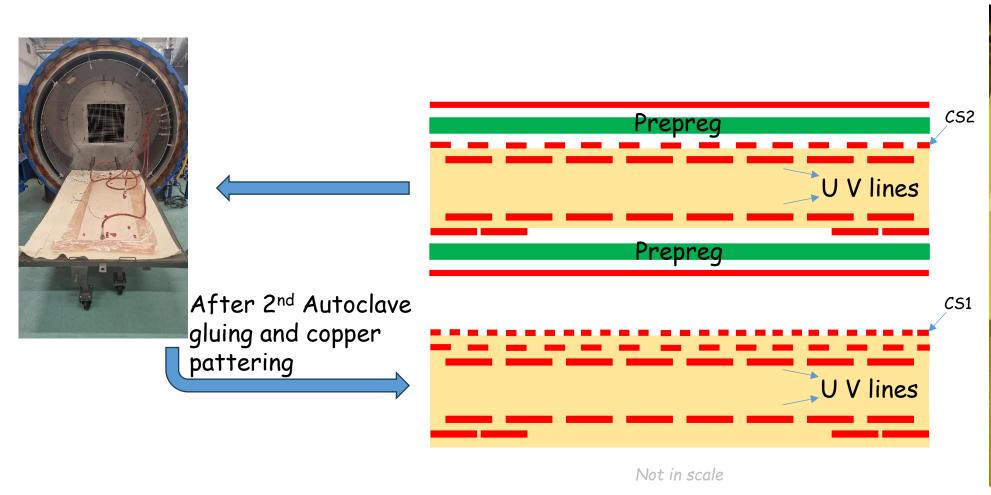


- 40-80 M $\Omega$ /square DLC resistive layer
- 2 capacitive sharing layers
- UV RO strips pitch 0,8



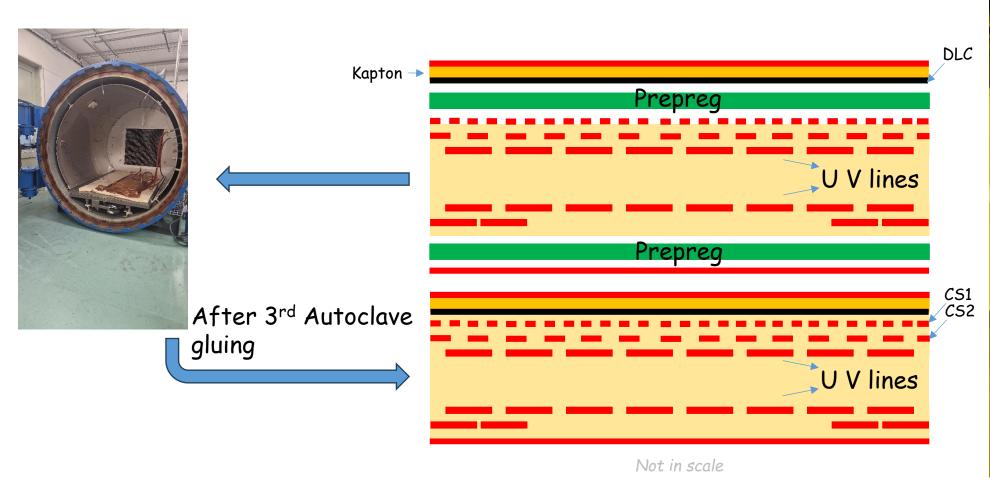


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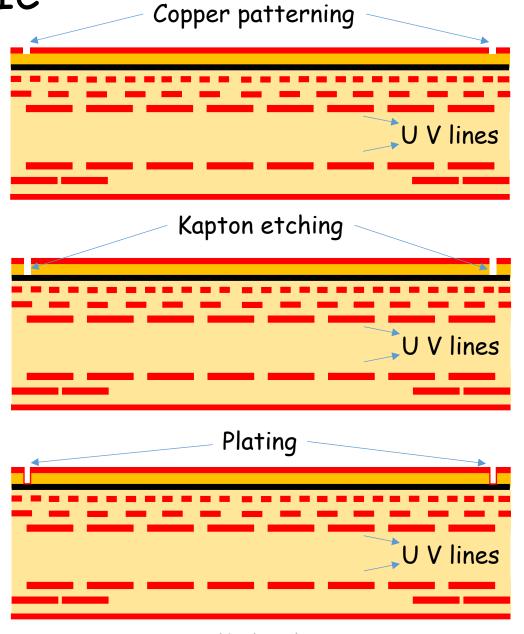


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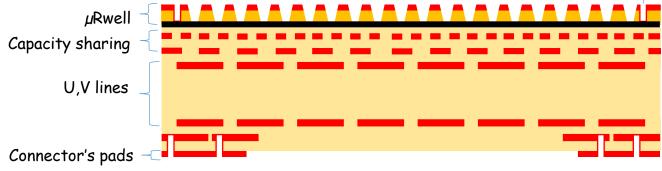
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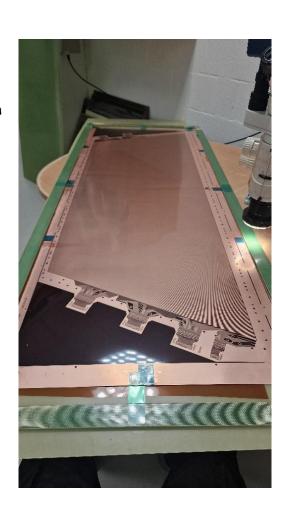




#### CLAS 12 µRWell 1 D

- $1,56 \times 0.55$ m total size  $\mu$ Rwell detector
- 20 to 70 Mohms/square DLC resistive layer
- Charge evacuation with strips
- 3 capacitive sharing layers
- V or U readout 1 mm pitch
- Total detector thickness lower than 300um





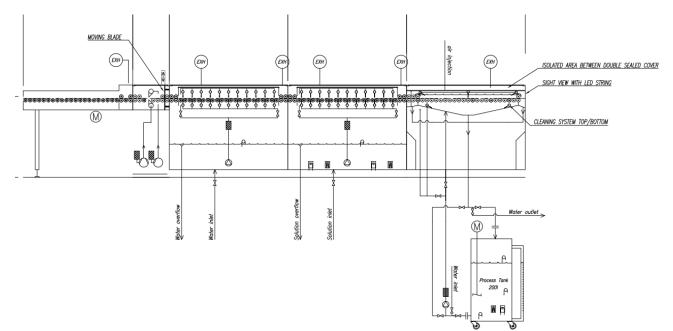
# <u>Future - Polyimide</u> etching machine

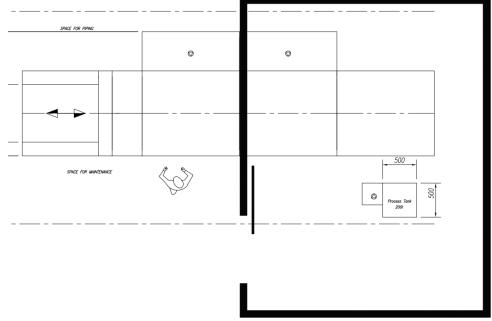
safe and easy process accessible by every technician in the workshop Reducing time -> cost size  $\le 1m \log n$ 

Not to replace dead bath but to industrialize the process





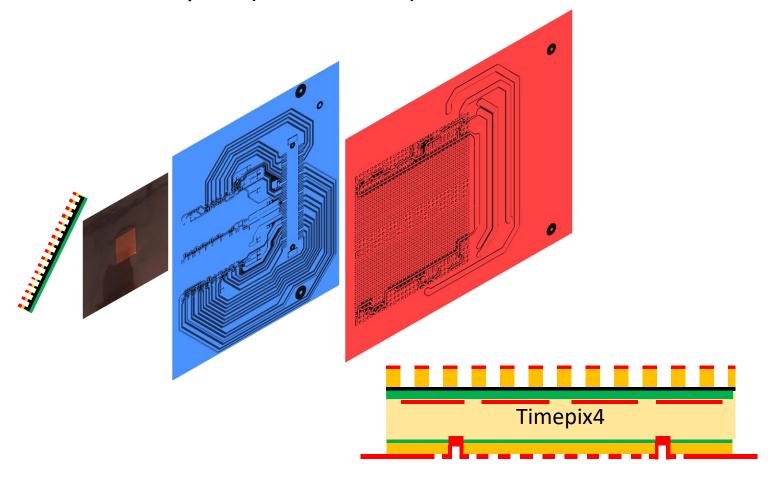




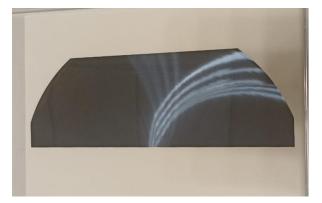
# Dziękuję

# Embedded silicon chip

• Timepix4 (25 x 28 mm) with uRwell



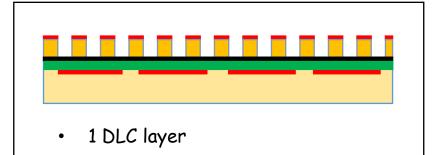
#### Large silicon chips 27 x 10 cm

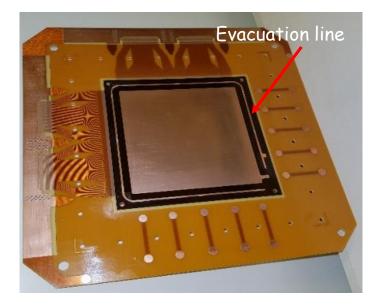






### Medium rate µRwell Lateral evacuation of charges





 $10 \text{cm} \times 10 \text{cm} \mu \text{Rwell detector}$  "STD kit"

#### High rate uRwell

Charge evacuation in the active area

